

REMARKS

Claims 1-20 are now present in this application. Claim 21 has been canceled.
Claims 1, 4 and 10 have been amended.

Reconsideration of this application, as amended, is respectfully requested.

CLAIM REJECTIONS – 35 U.S.C. §102

Claim 21 stands rejected under 35 U.S.C. 102(e) over Doyle. This rejection is respectfully traversed.

While not conceding to the appropriateness of the Examiner's rejection, Applicants respectfully submit that claim 21 has been canceled, thereby rendering the rejection thereof moot.

CLAIM REJECTIONS – 35 U.S.C. §103

Claims 1-9 and 10-20 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Doyle et al.(US Patent No. 6,025,254) in view of Broadbent et al. (IEEE Transactions on Electron Devices Vol. 36. No.11, November 1989). This rejection respectfully traversed.

A complete discussion of the Examiner's rejection is set forth in the Office Action, and is not being repeated here.

While not conceding to the appropriateness of the Examiner's rejection, Applicants have amended claim 1 to recite a combination of elements in a method of for forming a gate in a semiconductor device, including depositing a refractory metal layer on an entire surface such that the refractory metal layer is in contact with the top

surface of said non-silicide gate. Claim 10 has been similarly amended to recite a combination of elements in a method of fabricating a gate in a semiconductor device, including forming a refractory metal on said non-conductive silicide gate such that the refractory metal is in contact with the top surface of said non-silicide gate.

Doyle discloses a gate electrode layer 104, formed of polysilicon, and sidewall spacers 108, which are formed adjacent to gate electrode layer 104 (see Figs. 1(a)-1(e)). Figure 1(a) shows that a gate silicide layer 110 is formed on the gate electrode layer 104, and Figure 1(c) shows that a layer of nickel 116 is deposited on the gate silicide layer 110 and a sacrificial dielectric layer 114 covering a source/drain silicide layer formed on a substrate 102. Nickel layer 116 does not make contact with the gate electrode 104.

Therefore Doyle fails to disclose or suggest a combination of elements in a method for forming a gate in a semiconductor device, including depositing a refractory metal layer on an entire surface such that the refractory metal layer is in contact with the top surface of said non-silicide gate, as recited in independent claim 1, and similarly stated in independent claim 10. Broadbent cannot supply the deficiency of Doyle.

Claims 2-9 and 11-20 depend, either directly or indirectly on independent claims 1 and 10. Since neither Doyle, nor Broadbent discloses or suggests the above-recited features of independent claims 1 and 10, Doyle in view of Broadbent cannot render claims 1 – 20 obvious to one of ordinary skill in the art. Reconsideration and withdrawal of this art grounds of rejection is respectfully requested.

CONCLUSION

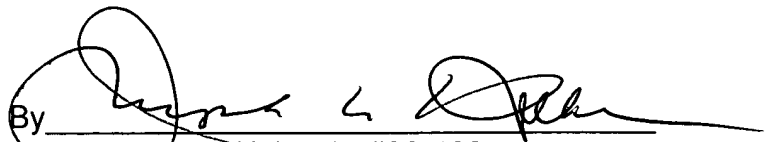
Should there be any outstanding matters that need to be resolved in the present application, the Examiner is respectfully requested to contact Percy L. Square (Reg. No. 51,084) at the telephone number of the undersigned below, to conduct an interview in an effort to expedite prosecution in connection with the present application.

Pursuant to 37 C.F.R. §§ 1.17 and 1.136(a), Applicant(s) respectfully petition(s) for a one (1) month extension of time for filing a reply in connection with the present application, and the required fee of \$110.00 is attached hereto.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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